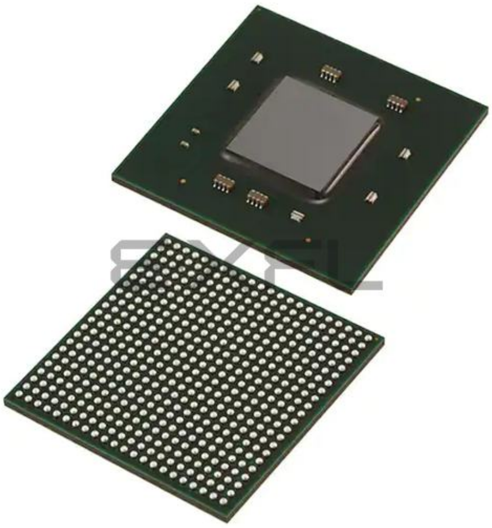
AMD Xilinx - XC7K160T-L2FBG484I Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	12675
Number of Logic Elements/Cells	162240
Total RAM Bits	11980800
Number of I/O	285
Number of Gates	-
Voltage - Supply	0.87V ~ 0.93V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k160t-l2fbg484i

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 2: **Recommended Operating Conditions** [1] *(Cont'd)*

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$[8]	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}[3]	Battery supply current	–	–	150	nA

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
R_{IN_TERM}(4)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), industrial (I), and extended (E) temperature devices	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

Table 4: **Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks(1)**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	61.7
V_{CCO} + 0.50	100	–0.50	25.8
V_{CCO} + 0.55	100	–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	100
V_{CCO} + 0.50	100	–0.50	100
V_{CCO} + 0.55	100	–0.55	100
V_{CCO} + 0.60	50.0	–0.60	50.0
V_{CCO} + 0.65	50.0	–0.65	50.0
V_{CCO} + 0.70	47.0	–0.70	50.0
V_{CCO} + 0.75	21.2	–0.75	50.0

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	**Description**	**Device**	**Speed Grade**				**Units**
			1.0V			**0.9V**	
			-3	**-2/-2L**	**-1**	**-2L**	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7K70T	6	6	6	6	mA
		XC7K160T	14	14	14	14	mA
		XC7K325T	19	19	19	19	mA
		XC7K355T	31	31	31	31	mA
		XC7K410T	34	34	34	34	mA
		XC7K420T	41	41	41	41	mA
		XC7K480T	41	41	41	41	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the XPower™ Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 10: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}(1)			V_{ID}(2)			V_{OCM}(3)			V_{OD}(4)		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO}–0.405	V_{CCO}–0.300	V_{CCO}–0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.
6. LVDS_25 is specified in Table 12.
7. LVDS is specified in Table 13.

Table 11: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}(1)			V_{ID}(2)		V_{OL}(3)	V_{OH}(4)	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HR I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 12: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage ($Q - \overline{Q}$), Q = High ($\overline{Q} - Q$), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage ($Q - \overline{Q}$), Q = High ($\overline{Q} - Q$), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 13: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		1.710	1.800	1.890	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage ($Q - \overline{Q}$), Q = High ($\overline{Q} - Q$), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage ($Q - \overline{Q}$), Q = High ($\overline{Q} - Q$), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.31	1.42	1.64	1.51	5.27	5.63	6.05	4.13	6.03	6.49	7.04	4.64	ns
LVTTL_S8	1.31	1.42	1.64	1.51	4.45	4.83	5.30	3.86	5.21	5.69	6.29	4.38	ns
LVTTL_S12	1.31	1.42	1.64	1.51	4.45	4.83	5.29	3.84	5.21	5.69	6.28	4.36	ns
LVTTL_S16	1.31	1.42	1.64	1.51	3.47	3.88	4.40	3.39	4.23	4.74	5.39	3.91	ns
LVTTL_S24	1.31	1.42	1.64	1.51	3.58	3.99	4.51	3.61	4.34	4.85	5.50	4.13	ns
LVTTL_F4	1.31	1.42	1.64	1.51	4.70	4.98	5.29	3.58	5.46	5.84	6.28	4.09	ns
LVTTL_F8	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.06	4.42	4.92	5.55	3.58	ns
LVTTL_F12	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.05	4.42	4.92	5.55	3.56	ns
LVTTL_F16	1.31	1.42	1.64	1.51	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVTTL_F24	1.31	1.42	1.64	1.51	2.41	2.64	2.89	2.94	3.17	3.50	3.88	3.45	ns
LVDS_25(1)	0.64	0.68	0.80	0.83	1.36	1.47	1.55	1.58	2.12	2.33	2.54	2.09	ns
MINI_LVDS_25	0.68	0.70	0.79	0.83	1.36	1.47	1.55	1.59	2.12	2.33	2.54	2.11	ns
BLVDS_25(1)	0.65	0.69	0.80	0.83	1.83	2.02	2.20	2.16	2.59	2.88	3.19	2.67	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	0.83	1.36	1.48	1.55	1.59	2.12	2.34	2.54	2.11	ns
PPDS_25(1)	0.65	0.69	0.80	0.83	1.36	1.49	1.58	1.59	2.12	2.35	2.57	2.11	ns
TMDS_33(1)	0.72	0.76	0.86	0.83	1.43	1.54	1.60	1.70	2.19	2.40	2.59	2.22	ns
PCI33_3(1)	1.28	1.41	1.65	1.50	2.71	3.08	3.52	3.42	3.47	3.94	4.51	3.94	ns
HSUL_12	0.63	0.64	0.71	0.79	2.06	2.31	2.59	2.13	2.82	3.17	3.58	2.64	ns
DIFF_HSUL_12	0.58	0.61	0.70	0.81	1.83	2.04	2.26	1.92	2.59	2.90	3.25	2.44	ns
HSTL_I_S	0.61	0.64	0.73	0.79	1.55	1.69	1.80	1.91	2.31	2.55	2.79	2.42	ns
HSTL_II_S	0.61	0.64	0.73	0.78	1.21	1.34	1.43	1.70	1.97	2.20	2.42	2.22	ns
HSTL_I_18_S	0.64	0.67	0.76	0.79	1.28	1.39	1.45	1.58	2.04	2.25	2.44	2.09	ns
HSTL_II_18_S	0.64	0.67	0.76	0.79	1.18	1.31	1.40	1.69	1.94	2.17	2.39	2.20	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	0.78	1.42	1.54	1.61	1.84	2.18	2.40	2.60	2.36	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	0.79	1.15	1.24	1.27	1.78	1.91	2.10	2.26	2.30	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	0.79	1.27	1.38	1.43	1.67	2.03	2.24	2.42	2.19	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	0.81	1.14	1.23	1.26	1.72	1.90	2.09	2.25	2.23	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
HSTL_I_F	0.61	0.64	0.73	0.79	1.10	1.19	1.23	1.41	1.86	2.05	2.22	1.92	ns
HSTL_II_F	0.61	0.64	0.73	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
HSTL_I_18_F	0.64	0.67	0.76	0.79	1.05	1.18	1.28	1.44	1.81	2.04	2.27	1.95	ns
HSTL_II_18_F	0.64	0.67	0.76	0.79	1.03	1.14	1.23	1.42	1.79	2.00	2.22	1.94	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	0.78	1.09	1.18	1.22	1.48	1.85	2.04	2.21	2.00	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	0.79	1.02	1.11	1.14	1.48	1.78	1.97	2.13	2.00	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	0.79	1.08	1.17	1.21	1.48	1.84	2.03	2.20	2.00	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	0.81	1.01	1.10	1.13	1.48	1.77	1.96	2.12	2.00	ns
LVCMOS33_S4	1.31	1.40	1.60	1.54	5.23	5.61	6.09	4.13	5.99	6.47	7.08	4.64	ns
LVCMOS33_S8	1.31	1.40	1.60	1.54	4.46	4.85	5.33	3.84	5.22	5.71	6.32	4.36	ns
LVCMOS33_S12	1.31	1.40	1.60	1.54	3.46	3.89	4.42	3.41	4.22	4.75	5.41	3.92	ns
LVCMOS33_S16	1.31	1.40	1.60	1.54	3.06	3.43	3.88	3.72	3.82	4.29	4.87	4.23	ns
LVCMOS33_F4	1.31	1.40	1.60	1.54	4.70	5.01	5.36	3.58	5.46	5.87	6.35	4.09	ns
LVCMOS33_F8	1.31	1.40	1.60	1.54	3.62	4.04	4.56	3.06	4.38	4.90	5.55	3.58	ns
LVCMOS33_F12	1.31	1.40	1.60	1.54	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVCMOS33_F16	1.31	1.40	1.60	1.54	2.44	2.69	2.96	2.88	3.20	3.55	3.95	3.39	ns
LVCMOS25_S4	1.08	1.16	1.32	1.36	4.49	4.80	5.16	3.44	5.25	5.66	6.15	3.95	ns
LVCMOS25_S8	1.08	1.16	1.32	1.36	3.66	4.04	4.49	3.20	4.42	4.90	5.48	3.72	ns
LVCMOS25_S12	1.08	1.16	1.32	1.36	2.77	3.10	3.49	2.80	3.53	3.96	4.48	3.31	ns
LVCMOS25_S16	1.08	1.16	1.32	1.36	3.24	3.62	4.09	3.14	4.00	4.48	5.08	3.66	ns
LVCMOS25_F4	1.08	1.16	1.32	1.36	3.96	4.31	4.72	3.06	4.72	5.17	5.71	3.58	ns
LVCMOS25_F8	1.08	1.16	1.32	1.36	2.43	2.87	3.42	2.50	3.19	3.73	4.41	3.02	ns
LVCMOS25_F12	1.08	1.16	1.32	1.36	2.23	2.63	3.13	2.48	2.99	3.49	4.12	3.00	ns
LVCMOS25_F16	1.08	1.16	1.32	1.36	1.92	2.17	2.45	2.33	2.68	3.03	3.44	2.84	ns
LVCMOS18_S4	0.64	0.66	0.74	0.87	3.24	3.45	3.66	1.91	4.00	4.31	4.65	2.42	ns
LVCMOS18_S8	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S12	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S16	0.64	0.66	0.74	0.87	1.82	2.03	2.24	1.84	2.58	2.89	3.23	2.36	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	0.87	1.74	1.92	2.08	1.92	2.50	2.78	3.07	2.44	ns
LVCMOS18_F4	0.64	0.66	0.74	0.87	3.12	3.31	3.49	1.77	3.88	4.17	4.48	2.28	ns
LVCMOS18_F8	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F12	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F16	0.64	0.66	0.74	0.87	1.52	1.68	1.81	1.72	2.28	2.54	2.80	2.23	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	0.87	1.34	1.46	1.55	1.66	2.10	2.32	2.54	2.17	ns
LVCMOS15_S4	0.66	0.69	0.81	0.90	3.48	3.74	4.03	2.22	4.24	4.60	5.02	2.73	ns
LVCMOS15_S8	0.66	0.69	0.81	0.90	2.37	2.67	3.01	2.41	3.13	3.53	4.00	2.92	ns
LVCMOS15_S12	0.66	0.69	0.81	0.90	1.83	2.03	2.23	1.91	2.59	2.89	3.22	2.42	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
DIFF_HSTL_II_DCI_F	0.75	0.79	0.92	0.76	0.97	1.08	1.15	1.30	1.61	1.84	1.97	1.91	ns
DIFF_HSTL_I_18_F	0.75	0.79	0.92	0.89	1.04	1.16	1.24	1.38	1.68	1.91	2.06	1.99	ns
DIFF_HSTL_II_18_F	0.75	0.79	0.92	0.89	0.98	1.09	1.16	1.40	1.62	1.85	1.98	2.01	ns
DIFF_HSTL_I_DCI_18_F	0.75	0.79	0.92	0.75	1.04	1.16	1.24	1.38	1.67	1.91	2.06	1.99	ns
DIFF_HSTL_II_DCI_18_F	0.75	0.79	0.92	0.75	0.98	1.09	1.16	1.33	1.61	1.85	1.98	1.94	ns
DIFF_HSTL_II _T_DCI_18_F	0.75	0.79	0.92	0.76	1.04	1.16	1.24	1.38	1.67	1.91	2.06	1.99	ns
LVCMOS18_S2	0.47	0.50	0.60	0.87	3.95	4.28	4.85	3.40	4.59	5.04	5.67	4.01	ns
LVCMOS18_S4	0.47	0.50	0.60	0.87	2.67	2.98	3.43	2.69	3.31	3.73	4.26	3.30	ns
LVCMOS18_S6	0.47	0.50	0.60	0.87	2.14	2.38	2.72	2.18	2.77	3.14	3.54	2.79	ns
LVCMOS18_S8	0.47	0.50	0.60	0.87	1.98	2.21	2.52	2.02	2.61	2.97	3.35	2.63	ns
LVCMOS18_S12	0.47	0.50	0.60	0.87	1.70	1.91	2.17	1.85	2.34	2.67	2.99	2.46	ns
LVCMOS18_S16	0.47	0.50	0.60	0.87	1.57	1.75	1.97	1.76	2.20	2.51	2.79	2.37	ns
LVCMOS18_F2	0.47	0.50	0.60	0.87	3.50	3.87	4.48	2.85	4.14	4.63	5.30	3.46	ns
LVCMOS18_F4	0.47	0.50	0.60	0.87	2.23	2.50	2.87	2.26	2.87	3.25	3.69	2.87	ns
LVCMOS18_F6	0.47	0.50	0.60	0.87	1.80	2.00	2.26	1.52	2.43	2.76	3.08	2.13	ns
LVCMOS18_F8	0.47	0.50	0.60	0.87	1.46	1.72	2.04	1.51	2.10	2.47	2.86	2.12	ns
LVCMOS18_F12	0.47	0.50	0.60	0.87	1.26	1.40	1.53	1.46	1.89	2.16	2.35	2.07	ns
LVCMOS18_F16	0.47	0.50	0.60	0.87	1.19	1.33	1.44	1.46	1.83	2.08	2.26	2.07	ns
LVCMOS15_S2	0.59	0.62	0.73	0.86	3.55	3.89	4.45	3.11	4.19	4.65	5.27	3.73	ns
LVCMOS15_S4	0.59	0.62	0.73	0.86	2.45	2.70	3.06	2.46	3.08	3.45	3.89	3.07	ns
LVCMOS15_S6	0.59	0.62	0.73	0.86	2.24	2.51	2.88	2.33	2.88	3.26	3.71	2.94	ns
LVCMOS15_S8	0.59	0.62	0.73	0.86	1.91	2.16	2.49	2.05	2.55	2.91	3.31	2.66	ns
LVCMOS15_S12	0.59	0.62	0.73	0.86	1.77	1.98	2.23	1.97	2.41	2.73	3.05	2.58	ns
LVCMOS15_S16	0.59	0.62	0.73	0.86	1.62	1.81	2.02	1.85	2.26	2.56	2.84	2.46	ns
LVCMOS15_F2	0.59	0.62	0.73	0.86	3.38	3.69	4.18	2.74	4.02	4.44	5.00	3.35	ns
LVCMOS15_F4	0.59	0.62	0.73	0.86	2.04	2.21	2.44	1.72	2.68	2.97	3.26	2.33	ns
LVCMOS15_F6	0.59	0.62	0.73	0.86	1.47	1.74	2.09	1.49	2.10	2.50	2.91	2.10	ns
LVCMOS15_F8	0.59	0.62	0.73	0.86	1.31	1.46	1.61	1.47	1.95	2.22	2.43	2.08	ns
LVCMOS15_F12	0.59	0.62	0.73	0.86	1.21	1.34	1.45	1.44	1.84	2.10	2.27	2.05	ns
LVCMOS15_F16	0.59	0.62	0.73	0.86	1.18	1.31	1.41	1.41	1.82	2.07	2.23	2.02	ns
LVCMOS12_S2	0.64	0.67	0.78	0.95	3.38	3.80	4.48	3.27	4.02	4.55	5.30	3.88	ns
LVCMOS12_S4	0.64	0.67	0.78	0.95	2.62	2.94	3.43	2.76	3.26	3.70	4.25	3.37	ns
LVCMOS12_S6	0.64	0.67	0.78	0.95	2.05	2.33	2.72	2.24	2.69	3.08	3.54	2.85	ns
LVCMOS12_S8	0.64	0.67	0.78	0.95	1.94	2.18	2.51	2.16	2.58	2.94	3.33	2.77	ns
LVCMOS12_F2	0.64	0.67	0.78	0.95	2.84	3.15	3.62	2.47	3.48	3.90	4.44	3.08	ns
LVCMOS12_F4	0.64	0.67	0.78	0.95	1.97	2.18	2.44	1.69	2.61	2.93	3.26	2.30	ns
LVCMOS12_F6	0.64	0.67	0.78	0.95	1.33	1.51	1.70	1.43	1.96	2.26	2.52	2.04	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVCMOS12_F8	0.64	0.67	0.78	0.95	1.27	1.42	1.55	1.41	1.91	2.18	2.37	2.02	ns
LVDCI_18	0.47	0.50	0.60	0.86	1.99	2.15	2.35	2.44	2.62	2.91	3.17	3.05	ns
LVDCI_15	0.59	0.62	0.73	0.87	1.98	2.23	2.58	2.40	2.62	2.99	3.40	3.01	ns
LVDCI_DV2_18	0.47	0.50	0.60	0.87	1.99	2.15	2.34	1.86	2.62	2.90	3.17	2.48	ns
LVDCI_DV2_15	0.59	0.62	0.73	0.87	1.98	2.23	2.58	1.83	2.62	2.99	3.40	2.44	ns
HSLVDCI_18	0.68	0.72	0.82	0.86	1.99	2.15	2.35	2.43	2.62	2.91	3.17	3.04	ns
HSLVDCI_15	0.68	0.72	0.82	0.84	1.98	2.23	2.58	2.27	2.62	2.99	3.40	2.88	ns
SSTL18_I_S	0.68	0.72	0.82	0.86	1.02	1.15	1.24	1.41	1.66	1.90	2.07	2.02	ns
SSTL18_II_S	0.68	0.72	0.82	0.87	1.17	1.29	1.37	1.55	1.81	2.05	2.19	2.16	ns
SSTL18_I_DCI_S	0.68	0.72	0.82	0.76	0.92	1.06	1.17	1.32	1.56	1.82	1.99	1.93	ns
SSTL18_II_DCI_S	0.68	0.72	0.82	0.78	0.88	0.98	1.08	1.26	1.51	1.74	1.90	1.87	ns
SSTL18_II_T_DCI_S	0.68	0.72	0.82	0.78	0.92	1.06	1.17	1.32	1.56	1.82	1.99	1.93	ns
SSTL15_S	0.68	0.72	0.82	0.81	0.94	1.06	1.15	1.32	1.58	1.82	1.97	1.93	ns
SSTL15_DCI_S	0.68	0.72	0.82	0.78	0.94	1.06	1.15	1.30	1.57	1.82	1.97	1.91	ns
SSTL15_T_DCI_S	0.68	0.72	0.82	0.80	0.94	1.06	1.15	1.30	1.57	1.82	1.97	1.91	ns
SSTL135_S	0.69	0.72	0.82	0.89	0.97	1.10	1.19	1.35	1.60	1.85	2.01	1.96	ns
SSTL135_DCI_S	0.69	0.72	0.82	0.84	0.97	1.09	1.19	1.33	1.60	1.85	2.01	1.94	ns
SSTL135_T_DCI_S	0.69	0.72	0.82	0.84	0.97	1.09	1.19	1.33	1.60	1.85	2.01	1.94	ns
SSTL12_S	0.69	0.72	0.82	0.95	0.96	1.09	1.18	1.33	1.60	1.84	2.00	1.94	ns
SSTL12_DCI_S	0.69	0.72	0.82	0.91	1.03	1.17	1.27	1.33	1.66	1.92	2.09	1.94	ns
SSTL12_T_DCI_S	0.69	0.72	0.82	0.91	1.03	1.17	1.27	1.33	1.66	1.92	2.09	1.94	ns
DIFF_SSTL18_I_S	0.75	0.79	0.92	0.89	1.02	1.15	1.24	1.43	1.66	1.90	2.07	2.04	ns
DIFF_SSTL18_II_S	0.75	0.79	0.92	0.89	1.17	1.29	1.37	1.55	1.81	2.05	2.19	2.16	ns
DIFF_SSTL18_I_DCI_S	0.75	0.79	0.92	0.76	0.92	1.06	1.17	1.40	1.56	1.82	1.99	2.01	ns
DIFF_SSTL18_II_DCI_S	0.75	0.79	0.92	0.75	0.88	0.98	1.08	1.33	1.51	1.74	1.90	1.94	ns
DIFF_SSTL18_II_T_DCI_S	0.75	0.79	0.92	0.76	0.92	1.06	1.17	1.40	1.56	1.82	1.99	2.01	ns
DIFF_SSTL15_S	0.68	0.72	0.82	0.89	0.94	1.06	1.15	1.32	1.58	1.82	1.97	1.93	ns
DIFF_SSTL15_DCI_S	0.68	0.72	0.82	0.75	0.94	1.06	1.15	1.30	1.57	1.82	1.97	1.91	ns
DIFF_SSTL15_T_DCI_S	0.68	0.72	0.82	0.76	0.94	1.06	1.15	1.38	1.57	1.82	1.97	1.99	ns
DIFF_SSTL135_S	0.69	0.72	0.82	0.91	0.97	1.10	1.19	1.35	1.60	1.85	2.01	1.96	ns
DIFF_SSTL135_DCI_S	0.69	0.72	0.82	0.76	0.97	1.09	1.19	1.33	1.60	1.85	2.01	1.94	ns
DIFF_SSTL135_T_DCI_S	0.69	0.72	0.82	0.76	0.97	1.09	1.19	1.43	1.60	1.85	2.01	2.04	ns
DIFF_SSTL12_S	0.69	0.72	0.82	0.91	0.96	1.09	1.18	1.33	1.60	1.84	2.00	1.94	ns
DIFF_SSTL12_DCI_S	0.69	0.72	0.82	0.78	1.03	1.17	1.27	1.33	1.66	1.92	2.09	1.94	ns
DIFF_SSTL12_T_DCI_S	0.69	0.72	0.82	0.80	1.03	1.17	1.27	1.41	1.66	1.92	2.09	2.02	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
SSTL18_I_F	0.68	0.72	0.82	0.86	0.94	1.06	1.15	1.32	1.58	1.82	1.97	1.93	ns
SSTL18_II_F	0.68	0.72	0.82	0.87	0.97	1.09	1.16	1.36	1.61	1.84	1.99	1.98	ns
SSTL18_I_DCI_F	0.68	0.72	0.82	0.76	0.89	1.02	1.10	1.30	1.53	1.77	1.92	1.91	ns
SSTL18_II_DCI_F	0.68	0.72	0.82	0.78	0.89	1.02	1.10	1.24	1.53	1.77	1.92	1.85	ns
SSTL18_II_T_DCI_F	0.68	0.72	0.82	0.78	0.89	1.02	1.10	1.27	1.53	1.77	1.92	1.88	ns
SSTL15_F	0.68	0.72	0.82	0.81	0.89	1.01	1.09	1.24	1.53	1.77	1.91	1.85	ns
SSTL15_DCI_F	0.68	0.72	0.82	0.78	0.89	1.01	1.09	1.27	1.53	1.77	1.91	1.88	ns
SSTL15_T_DCI_F	0.68	0.72	0.82	0.80	0.89	1.01	1.09	1.27	1.53	1.77	1.91	1.88	ns
SSTL135_F	0.69	0.72	0.82	0.89	0.88	1.00	1.08	1.27	1.52	1.76	1.90	1.88	ns
SSTL135_DCI_F	0.69	0.72	0.82	0.84	0.89	1.00	1.08	1.27	1.52	1.76	1.90	1.88	ns
SSTL135_T_DCI_F	0.69	0.72	0.82	0.84	0.89	1.00	1.08	1.27	1.52	1.76	1.90	1.88	ns
SSTL12_F	0.69	0.72	0.82	0.95	0.88	1.00	1.08	1.26	1.52	1.76	1.90	1.87	ns
SSTL12_DCI_F	0.69	0.72	0.82	0.91	0.91	1.03	1.11	1.24	1.54	1.79	1.93	1.85	ns
SSTL12_T_DCI_F	0.69	0.72	0.82	0.91	0.91	1.03	1.11	1.26	1.54	1.79	1.93	1.87	ns
DIFF_SSTL18_I_F	0.75	0.79	0.92	0.89	0.94	1.06	1.15	1.38	1.58	1.82	1.97	1.99	ns
DIFF_SSTL18_II_F	0.75	0.79	0.92	0.89	0.97	1.09	1.16	1.40	1.61	1.84	1.99	2.01	ns
DIFF_SSTL18_I_DCI_F	0.75	0.79	0.92	0.76	0.89	1.02	1.10	1.36	1.53	1.77	1.92	1.98	ns
DIFF_SSTL18_II_DCI_F	0.75	0.79	0.92	0.75	0.89	1.02	1.10	1.32	1.53	1.77	1.92	1.93	ns
DIFF_SSTL18_II_T_DCI_F	0.75	0.79	0.92	0.76	0.89	1.02	1.10	1.38	1.53	1.77	1.92	1.99	ns
DIFF_SSTL15_F	0.68	0.72	0.82	0.89	0.89	1.01	1.09	1.24	1.53	1.77	1.91	1.85	ns
DIFF_SSTL15_DCI_F	0.68	0.72	0.82	0.75	0.89	1.01	1.09	1.27	1.53	1.77	1.91	1.88	ns
DIFF_SSTL15_T_DCI_F	0.68	0.72	0.82	0.76	0.89	1.01	1.09	1.35	1.53	1.77	1.91	1.96	ns
DIFF_SSTL135_F	0.69	0.72	0.82	0.91	0.88	1.00	1.08	1.27	1.52	1.76	1.90	1.88	ns
DIFF_SSTL135_DCI_F	0.69	0.72	0.82	0.76	0.89	1.00	1.08	1.27	1.52	1.76	1.90	1.88	ns
DIFF_SSTL135_T_DCI_F	0.69	0.72	0.82	0.76	0.89	1.00	1.08	1.35	1.52	1.76	1.90	1.96	ns
DIFF_SSTL12_F	0.69	0.72	0.82	0.91	0.88	1.00	1.08	1.26	1.52	1.76	1.90	1.87	ns
DIFF_SSTL12_DCI_F	0.69	0.72	0.82	0.78	0.91	1.03	1.11	1.24	1.54	1.79	1.93	1.85	ns
DIFF_SSTL12_T_DCI_F	0.69	0.72	0.82	0.80	0.91	1.03	1.11	1.33	1.54	1.79	1.93	1.94	ns

Notes:

1. This I/O standard is only available in the 1.8V high-performance (HP) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Table 27: **IO_FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T_{OFFCKO_DO}	RDCLK to Q outputs	0.51	0.56	0.63	0.81	ns
T_{CKO_FLAGS}	Clock to IO_FIFO Flags	0.59	0.62	0.81	0.77	ns
Setup/Hold						
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK	0.43/–0.01	0.47/–0.01	0.53/–0.01	0.76/–0.05	ns
$T_{IFFCCK\_WREN}/T_{IFFCKC\_WREN}$	WREN to WRCLK	0.39/–0.01	0.43/–0.01	0.50/–0.01	0.70/–0.05	ns
$T_{OFFCCK\_RDEN}/T_{OFFCKC\_RDEN}$	RDEN to RDCLK	0.49/0.01	0.53/0.02	0.61/0.02	0.79/–0.02	ns
Minimum Pulse Width						
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
Maximum Frequency						
F_{MAX}	RDCLK and WRCLK	533.05	470.37	400.00	333.33	MHz

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 29: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{SHCKO}	Clock to A – B outputs	0.68	0.70	0.85	1.08	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	0.91	0.95	1.15	1.44	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK	0.45/0.23	0.45/0.24	0.54/0.27	0.69/0.33	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock	0.13/0.50	0.14/0.50	0.17/0.58	0.21/0.63	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.40/0.16	0.42/0.17	0.52/0.23	0.63/0.23	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock	0.29/0.09	0.30/0.09	0.36/0.09	0.46/0.10	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK	0.29/0.09	0.30/0.09	0.37/0.09	0.47/0.10	ns, Min
Clock CLK						
T_{MPW}	Minimum pulse width	0.68	0.77	0.91	1.11	ns, Min
T_{MCP}	Minimum clock period	1.35	1.54	1.82	2.22	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 30: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	0.96	0.98	1.20	1.35	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.19	1.23	1.50	1.72	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	0.89	0.91	1.10	1.25	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{WS\_SHFREG}/T_{WH\_SHFREG}$	WE input	0.26/0.09	0.27/0.09	0.33/0.09	0.41/0.10	ns, Min
$T_{CECK\_SHFREG}/T_{CKCE\_SHFREG}$	CE input to CLK	0.27/0.09	0.28/0.09	0.33/0.09	0.42/0.10	ns, Min
$T_{DS\_SHFREG}/T_{DH\_SHFREG}$	A – D inputs to CLK	0.28/0.26	0.28/0.26	0.33/0.30	0.41/0.36	ns, Min
Clock CLK						
T_{MPW_SHFREG}	Minimum pulse width	0.55	0.65	0.78	0.91	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.

Block RAM and FIFO Switching Characteristics

Table 31: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$(1)	Clock CLK to DOUT output (without output register)(2)(3)	1.57	1.80	2.08	2.44	ns, Max
	Clock CLK to DOUT output (with output register)(4)(5)	0.54	0.63	0.75	0.86	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register)(2)(3)	2.35	2.58	3.26	4.49	ns, Max
	Clock CLK to DOUT output with ECC (with output register)(4)(5)	0.62	0.69	0.80	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with Cascade (without output register)(2)	2.21	2.45	2.80	3.19	ns, Max
	Clock CLK to DOUT output with Cascade (with output register)(4)	0.98	1.08	1.24	1.32	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs(6)	0.65	0.74	0.89	0.97	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs(7)	0.79	0.87	0.98	1.10	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode	0.66	0.72	0.80	0.93	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register)	2.17	2.38	3.01	4.15	ns, Max
	Clock CLK to BITERR (with output register)	0.57	0.65	0.76	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register)	0.64	0.74	0.90	0.98	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.71	0.79	0.92	1.10	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{RCCK_ADDRA}/T_{RCKC_ADDRA}	ADDR inputs(8)	0.38/0.27	0.42/0.28	0.48/0.31	0.65/0.38	ns, Min
$T_{RDCK\_DI\_WF\_NC}$/ $T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode(9)	0.49/0.51	0.55/0.53	0.63/0.57	0.78/0.64	ns, Min
$T_{RDCK\_DI\_RF}$/$T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode(9)	0.17/0.25	0.19/0.29	0.21/0.35	0.25/0.32	ns, Min
$T_{RDCK\_DI\_ECC}$/ $T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode(9)	0.42/0.37	0.47/0.39	0.53/0.43	0.66/0.46	ns, Min
$T_{RDCK\_DI\_ECCW}$/ $T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only(9)	0.79/0.37	0.87/0.39	0.99/0.43	1.17/0.41	ns, Min
$T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode(9)	0.89/0.47	0.98/0.50	1.12/0.54	1.32/0.65	ns, Min
$T_{RCCK\_INJECTBITERR}$/ $T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode	0.49/0.30	0.55/0.31	0.63/0.34	0.78/0.41	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM Enable (EN) input	0.30/0.17	0.33/0.18	0.38/0.20	0.48/0.22	ns, Min
T_{RCCK_REGCE}/T_{RCKC_REGCE}	CE input of output register	0.21/0.13	0.25/0.13	0.31/0.14	0.34/0.16	ns, Min
T_{RCCK_RSTREG}/T_{RCKC_RSTREG}	Synchronous RSTREG input	0.25/0.06	0.27/0.06	0.29/0.06	0.35/0.06	ns, Min

Table 36: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.12	ns
$T_{BHCCK\_CE}/T_{BHCKC\_CE}$	CE pin Setup and Hold	0.20/0.16	0.23/0.20	0.38/0.21	0.28/0.09	ns
Maximum Frequency						
F_{MAX_BUFH}	Horizontal clock buffer (BUFH)	741.00	710.00	625.00	560.00	MHz

Table 37: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
T_{DCD_CLK}	Global Clock Tree Duty Cycle Distortion(1)	All	0.20	0.20	0.20	0.25	ns
T_{CKSKEW}	Global Clock Tree Skew(2)	XC7K70T	0.29	0.40	0.40	0.47	ns
		XC7K160T	0.42	0.53	0.57	0.59	ns
		XC7K325T	0.59	0.74	0.79	0.91	ns
		XC7K355T	0.45	0.57	0.59	0.69	ns
		XC7K410T	0.60	0.74	0.79	0.91	ns
		XC7K420T	0.60	0.74	0.79	0.91	ns
		XC7K480T	0.60	0.74	0.79	0.91	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion	All	0.12	0.12	0.12	0.12	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region	All	0.02	0.02	0.02	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion	All	0.15	0.15	0.15	0.15	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx Timing Analyzer tools to evaluate clock skew specific to your application.

Table 42: Clock-Capable Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* MMCM.							
$T_{ICKOFMMCMCC}$	Clock-capable clock input and OUTFF *with* MMCM	XC7K70T	0.95	0.95	0.95	1.74	ns
		XC7K160T	0.96	0.96	0.96	1.78	ns
		XC7K325T	1.00	1.00	1.00	1.82	ns
		XC7K355T	1.00	1.00	1.00	1.78	ns
		XC7K410T	1.00	1.00	1.00	1.82	ns
		XC7K420T	1.07	1.07	1.07	1.82	ns
		XC7K480T	1.07	1.07	1.07	1.82	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 43: Clock-Capable Clock Input to Output Delay With PLL

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.							
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL	XC7K70T	0.84	0.84	0.84	1.45	ns
		XC7K160T	0.89	0.89	0.89	1.54	ns
		XC7K325T	0.89	0.89	0.89	1.54	ns
		XC7K355T	0.89	0.89	0.89	1.50	ns
		XC7K410T	0.89	0.89	0.89	1.54	ns
		XC7K420T	0.96	0.96	0.96	1.54	ns
		XC7K480T	0.96	0.96	0.96	1.54	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 44: Pin-to-Pin, Clock-to-Out using BUFIO

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* BUFIO.						
$T_{ICKOFCS}$	Clock-to-Out of I/O clock for HR I/O banks	4.93	5.52	6.20	6.97	ns
	Clock-to-Out of I/O clock for HP I/O banks	4.85	5.44	6.11	6.90	ns

Table 53: GTX Transceiver Performance *(Cont'd)*

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1[1]		-2L[2]		
			Package Type								
			FF	FB	FF	FB	FF	FB	FF	FB	
$F_{GQPLLRANGE2}$	GTX transceiver QPLL frequency range 2		9.8–12.5		9.8–10.3125		N/A		N/A		GHz

Notes:

1. The -1 speed grade requires a 4-byte internal data width for operation above 5.0 Gb/s.
2. The -2L (0.9V) speed grade requires a 4-byte internal data width for operation above 3.8 Gb/s.
3. Data rates between 8.0 Gb/s and 9.8 Gb/s are not available.
4. For QPLL line rate range 2, the maximum line rate with the divider N set to 66 is 10.3125Gb/s.

Table 54: GTX Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$F_{GTXDRPCLK}$	GTXDRPCLK maximum frequency	175.01	175.01	156.25	125.00	MHz

Table 55: GTX Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range	-3 speed grade	60	–	700	MHz
		All other speed grades	60	–	670	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	40	50	60	%

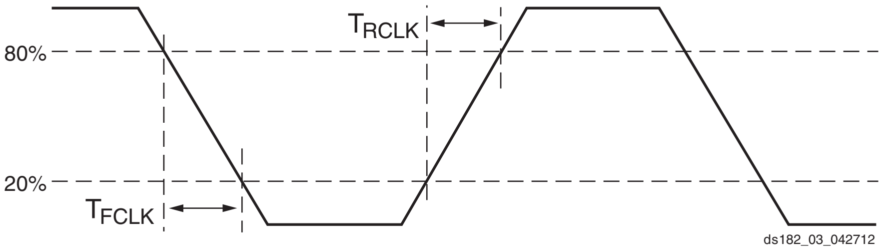

Figure 3: **Reference Clock Timing Parameters**

Table 67: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
XADC Reference[5]						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, $T_j = -40°C$ to 100°C	1.2375	1.25	1.2625	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for new BitGen option XADCEnhancedLinearity = ON.
3. See the ADC chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
4. See the Timing chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted. On-chip reference variation is ±1%.

Configuration Switching Characteristics

Table 68: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Power-up Timing Characteristics						
T_{PL}[1]	Program latency	5	5	5	5	ms, Max
T_{POR}[1]	Power-on reset (50 ms ramp rate time)	10/50	10/50	10/50	10/50	ms, Min/Max
	Power-on reset (1 ms ramp rate time)	10/35	10/35	10/35	10/35	ms, Min/Max
$T_{PROGRAM}$	Program pulse width	250	250	250	250	ns, Min
CCLK Output (Master Mode)						
T_{ICCK}	Master CCLK output delay	150	150	150	150	ns, Min
T_{MCCKL}	Master CCLK clock Low time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
T_{MCCKH}	Master CCLK clock High time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
F_{MCCK}	Master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
	Master CCLK frequency for AES encrypted x16	50.00	50.00	50.00	35.00	MHz, Max
F_{MCCK_START}	Master CCLK frequency at start of configuration	3.00	3.00	3.00	3.00	MHz, Typ
$F_{MCCKTOL}$	Frequency tolerance, master mode with respect to nominal CCLK	±50	±50	±50	±50	%, Max
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	2.50	2.50	2.50	2.50	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	2.50	2.50	2.50	2.50	ns, Min
F_{SCCK}	Slave CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
EMCCLK Input (Master Mode)						
T_{EMCCKL}	External master CCLK Low time	2.50	2.50	2.50	2.50	ns, Min
T_{EMCCKH}	External master CCLK High time	2.50	2.50	2.50	2.50	ns, Min
F_{EMCCK}	External master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2)	100.00	100.00	100.00	70.00	MHz, Max

Revision History

The following table shows the revision history for this document:

Date	Version	Description
03/01/11	1.0	Initial Xilinx release.
04/01/11	1.1	Added the XC7K355T, XC7K420T, and XC7K480T devices throughout data sheet. Added the extended temperature range discussion to page 1. Updated V_{CCAUX_IO} in Table 2. Edits to clarify Power-On/Off Power Supply Sequencing power sequencing discussion. Added I_{CCAUX_IO} and I_{CCBRAM} to Table 6 and Table 7. Updated MMCM_F_{INDUTY} and added $F_{INJITTER}$, $T_{OUTJITTER}$, $T_{EXTFDVAR}$, and Note 3 to Table 38. Removed the SBG324 package from Table 50. Updated the Notice of Disclaimer.
10/04/11	1.2	Replaced -1L with -2L throughout this data sheet. Updated Min/Max values and removed Note 5 from Table 2. Clarified Power-On/Off Power Supply Sequencing power sequencing discussion including adding $T_{VCCO2VCCAUX}$ to Table 8. Updated V_{ICM} in Table 12 and Table 13. Added Note 1 to table 12. Updated Table 69 including adding Note 1. Added *Absolute Maximum Ratings for GTX Transceivers*. Revised the reference clock maximum frequency (F_{GCLK}) in Table 55. Added Table 57. Added LVTTL and removed SSTL135_II and SSTL15_II specifications from Table 19. Removed HSTL_III from Table 20. Removed the *I/O Standard Adjustment Measurement Methodology* section. Use IBIS for more accurate information and measurements. Updated $T_{IDELAYPAT\_JIT}$ in Table 26. Added T_{AS}/T_{AH} to Table 28. Added $T_{RDCK\_DI\_WF\_NC}$/$T_{RCKD\_DI\_WF\_NC}$ and $T_{RDCK\_DI\_RF}$/$T_{RCKD\_DI\_RF}$ to Table 31. Completely updated Table 68. Updated the AC Switching Characteristics in Table 19, Table 20, Table 21, Table 22, Table 23, Table 24, Table 26 through Table 38, Table 40 though Table 37, and Table 67.
11/03/11	1.3	Revised the V_{OCM} specification in Table 12. Updated the AC Switching Characteristics based upon the ISE 13.3 v1.02 speed specification throughout document including Table 19 and Table 20. Added MMCM_$T_{FBDELAY}$ while adding MMCM_ to the symbol names of a few specifications in Table 38 and PLL to the symbol names in Table 39. In Table 40 through Table 47, updated the pin-to-pin descriptions with the SSTL15 standard. Updated units in Table 49.
02/13/12	1.4	Updated summary description on page 1. In Table 2, revised V_{CCO} for the 3.3V HR I/O banks and updated T_j. Added typical values to Table 3. Updated the notes in Table 6. Added MGTAVCC, MGTAVTT, and MGTVCCAUX power supply ramp times to Table 8. Rearranged Table 9, added Mobile_DDR, HSTL_I_18, HSTL_II_18, HSUL_12, SSTL135_R, SSTL15_R, and SSTL12 and removed DIFF_SSTL135, DIFF_SSTL18_I, DIFF_SSTL18_II, DIFF_HSTL_I, and DIFF_HSTL_II. Added Table 10 and Table 11. Revised the specifications in Table 12 and Table 13. Updated the eFUSE Programming Conditions section and removed the endurance table. Added the IO_FIFO Switching Characteristics table. Revised I_{CCADC} and updated Note 1 in Table 67. Revised DDR LVDS transmitter data width in Table 16. Updated the AC Switching Characteristics based upon the ISE 13.4 v1.03 speed specification throughout document. Removed notes from Table 28 as they are no longer applicable. Updated specifications in Table 68. Updated Note 1 in Table 37. In the GTX Transceiver DC Input and Output Levels section: Revised V_{IN}, and added I_{DCIN} and I_{DCOUT} to Table 51. Added Note 4 to Table 53. In Table 55, revised F_{GCLK}, removed T_{PHASE}, and added T_{DLOCK}. Revised specifications and added Note 2 to Table 57. Added Table 58 and Table 59 along with GTX Transceiver Protocol Jitter Characteristics in Table 60 through Table 65.
05/23/12	1.5	Reorganized entire data sheet including adding Table 44 and Table 48. Updated T_{SOL} in Table 1. Updated I_{BATT} and added R_{IN_TERM} to Table 3. Added values to Table 6 and Table 7. Updated Power-On/Off Power Supply Sequencing, page 6 with regards to GTX transceivers. Updated many parameters in Table 9 including SSTL135 and SSTL135_R. Removed V_{OX} column and added DIFF_HSUL_12 to Table 11. Updated V_{OL} in Table 12. Updated Table 16 and removed notes 2 and 3. Updated Table 17. Updated the AC Switching Characteristics based upon the ISE 14.1 v1.04 for the -3, -2, -2L (1.0V), -1, and -2L (0.9V) speed specifications throughout the document. In Table 31, updated Reset Delays section including Note 10 and Note 11. Added data for T_{LOCK} and T_{DLOCK} in Table 55. Updated many of the XADC specifications in Table 67 and added Note 2. Updated and moved *Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK* section from Table 68 to Table 38 and Table 39.

Date	Version	Description
07/25/12	1.6	Updated the descriptions, changed V_{IN} and Note 2 and added Note 4 in Table 1. In Table 2, changed descriptions and notes, removed Note 7, changed GTX transceiver parameters and values and added Note 9. Updated parameters in Table 3. Added Table 4 and Table 5. Changed the typical values for many of the devices in Table 7. Updated LVCMOS12 and the SSTLs in Table 9. Updated many of the specifications in Table 10 and Table 11. Updated speed specification to v1.06 (-3, -2, -2L(1.0V), -1) and v1.05 (-2L(0.9V)) with appropriate changes to Table 14 and Table 15 including production release of the XC7K325T and the XC7K410T in the -2, -2L(1.0V), and -1 speed designations. Added notes and specifications to Table 17 and Table 18. Updated the IOB Pad Input/Output/3-State discussion and changed Table 21 by adding $T_{IOIBUFDISABLE}$. Removed many of the combinatorial delay specifications and T_{CINCK}/T_{CKCIN} from Table 28. Rearranged Table 51 including moving some parameters to Table 1. Added Table 56. Updated Table 57. In Table 59, updated SJ Jitter Tolerance with Stressed Eye section, page 51 and Note 8. Added Note 1, Note 2, and Note 3 to Table 62. Added Note 1 and Note 2 to Table 63, and line rate ranges. Updated Table 64 including adding Note 1. Updated Table 65 including adding Note 1. In Table 67 updated Note 1 and added Note 4. In Table 68, updated T_{POR} and F_{EMCCK}.
09/04/12	1.7	Updated Table 14 and Table 15 for production release of the XC7K160T in the -2, -2L(1.0V), and -1 speed designations.
09/26/12	1.8	In Table 2, revised V_{CCINT} and V_{CCBRAM} and added Note 2. Updated Table 14 and Table 15 for production release of the XC7K480T in the -2, -2L(1.0V), and -1 speed designations and the XC7K325T and XC7K410T in the -3 speed designation.
10/10/12	1.9	Updated the $I_{CCINTMIN}$ value for the XC7K355T in Table 7. Updated Table 14 and Table 15 for production release of the XC7K420T in the -2, -2L(1.0V), and -1 speed designations.
10/25/12	2.0	Updated the AC Switching Characteristics based upon ISE 14.3 v1.07 for the -3, -2, -2L (1.0V), -1 speed specifications, and ISE 14.3 v1.06 for the -2L (0.9V) speed specifications throughout the document. Updated Table 14 and Table 15 for production release of the XC7K355T in the -2, -2L(1.0V), and -1 speed designations. Also updated Table 14 and Table 15 for production release of the XC7K325T and XC7K410T in the -2L (0.9V). Added values for Table 16 -2L (0.9V). Added package skew values to Table 50. In Table 53, increased -1 speed grade (FF package) F_{GTXMAX} value from 6.6 Gb/s to 8.0 Gb/s.
10/31/12	2.1	Updated Table 14 and Table 15 for production release of the XC7K70T in the -2, -2L(1.0V), and -1 speed designations.
11/26/12	2.2	Updated Table 14 and Table 15 for production release of -3 speed designation for XC7K70T, XC7K160T, XC7K355T, XC7K420T, and XC7K480T. Removed Note 4 from Table 67.
12/05/12	2.3	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K160T, XC7K420T, and XC7K480T. Updated Note 1 in Table 50.
12/12/12	2.4	Updated Table 14 and Table 15 for production release of the -2L (0.9V) speed designation for XC7K70T and XC7K355T. Added Internal Configuration Access Port section to Table 68.